



DPLS320A

LOW V_{CE(SAT)} PNP SURFACE MOUNT TRANSISTOR

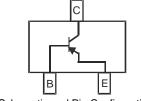
Features

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Complimentary NPN Type Available (DNLS320A)
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)





Schematic and Pin Configuration

Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-20	V
Collector-Emitter Voltage	V _{CEO}	-20	V
Emitter-Base Voltage	V _{EBO}	-5	V
Peak Pulse Current	I _{CM}	-5	A
Repetitive Peak Pulse Current (Note 3)	I _{CRP}	-3	A
Continuous Collector Current	I _C	-2	A
Base Current	Ι _Β	-0.5	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ T _A = 25°C	PD	600	mW
Thermal Resistance, Junction to Ambient Air (Note 3) @ T _A = 25°C	R _{0JA}	209	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

1. No purposefully added lead.

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

3. Operated under pulsed conditions: pulse width \leq 100ms, duty cycle \leq 0.25.

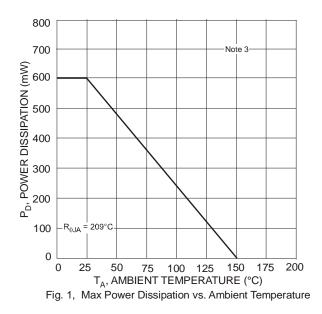
4. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

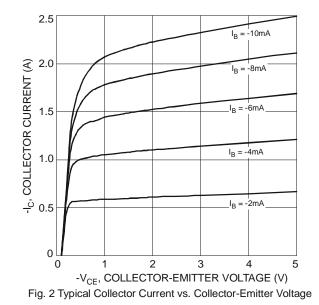


Electrical Characteristics $@T_A = 25^{\circ}C$ unless otherwise specified

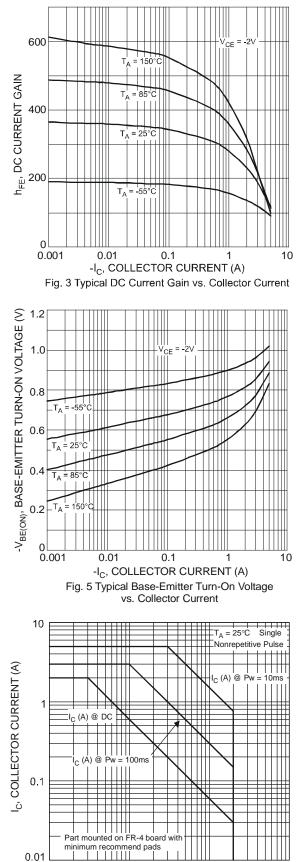
			-			T (0)
Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 5)			1	1	1	Γ
Collector-Base Cutoff Current	Ісво		—	-100	nA	$V_{CB} = -20V, I_E = 0$
	ЮВО	_	_	-50	μΑ	$V_{CB} = -20V, I_E = 0, T_A = 150^{\circ}C$
Emitter-Base Cutoff Current	I _{EBO}			-100	nA	$V_{EB} = -5V, I_{C} = 0$
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-20	—		V	I _C = -100μA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-20	—		V	I _C = -10mA
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5	—		V	I _E = -100μA
ON CHARACTERISTICS (Note 5)						
		220	—			$V_{CE} = -2V, I_{C} = -0.1A$
		220	—			$V_{CE} = -2V, I_{C} = -0.5A$
DC Current Gain	h _{FE}	200	_		1 —	$V_{CE} = -2V, I_{C} = -1A$
		150	_			$V_{CE} = -2V, I_{C} = -2A$
		100	_			$V_{CE} = -2V, I_{C} = -3A$
			—	-80		$I_{C} = -0.5A, I_{B} = -50mA$
		_	_	-150	1	I _C = -1A, I _B = -50mA
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		_	-250	mV	I _C = -2A, I _B = -100mA
			—	-230		$I_{\rm C} = -2A, I_{\rm B} = -200 {\rm mA}$
			_	-330		I _C = -3A, I _B = -300mA
Equivalent On-Resistance	R _{CE(SAT)}		90	115	mΩ	I _E = -2A, I _B = -200mA
Base-Emitter Saturation Voltage		_	_	-1.1	V	I _C = -2A, I _B = -100mA
Base-Emilier Saluration Voltage	V _{BE(SAT)}	_	_	-1.2	V	I _C = -3A, I _B = -300mA
Base-Emitter Turn-on Voltage	V _{BE(ON)}			-1.2	V	$V_{CE} = -2V, I_{C} = -1A$
SMALL SIGNAL CHARACTERISTICS	· · · ·					
Transition Frequency	f _T	100	215	_	MHz	V _{CE} = -5V, I _C = -100mA, f = 100MHz
Output Capacitance	C _{ob}		—	50	pF	V _{CB} = -10V, f = 1MHz

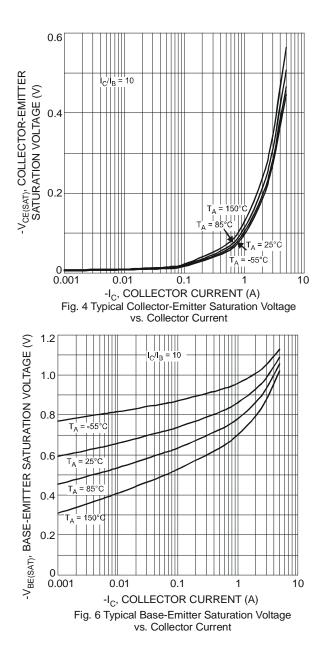
Notes: 5. Measured under pulsed conditions. Pulse width = 300μ s. Duty cycle $\leq 2\%$.











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V_{CE}, COLLECTOR-EMITTER VOLTAGE (V) Fig. 7 Safe Operation Area 100

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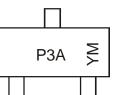


Ordering Information (Note 6)

Device	Packaging	Shipping
DPLS320A-7	SOT-23	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

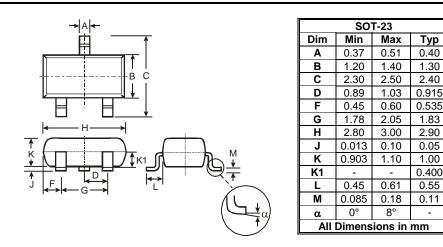


P3A = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

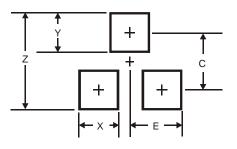
Data Car

Date Code Key												
Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Y	Z		А	В		С
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D

Package Outline Dimensions



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

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